

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7	(substrate and source and drain and channel and gate and semiconductor and (crystal adj grain) and ((thin adj film adj transistor) TFT finfet) and (gate adj (film insulat\$4 dielectric)) and first and second).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 13:29
L2	12	(substrate and source and drain and channel and gate and semiconductor and (crystal adj grain) and ((thin adj film adj transistor) TFT finfet) and (gate adj (film insulat\$4 dielectric))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 13:36
L3	5	(substrate and source and drain and channel and gate and semiconductor and (crystal adj grain) and ((thin adj film adj transistor) TFT finfet) and (gate adj (film insulat\$4 dielectric))).clm. not l1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 13:30
L4	1223	(substrate and source and drain and channel and gate and semiconductor and ((thin adj film adj transistor) TFT finfet) and (gate adj (film insulat\$4 dielectric))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 13:36
L5	629	(substrate and source and drain and channel and gate and semiconductor and ((thin adj film adj transistor) TFT finfet) and (gate adj (film insulat\$4 dielectric))).clm. and cryst\$6.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 13:37
L6	490	(substrate and source and drain and channel and gate and semiconductor and ((thin adj film adj transistor) TFT finfet) and (gate adj (film insulat\$4 dielectric)) and first and second).clm. and cryst\$6.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 13:41